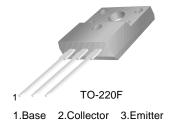


KSD2012

Low Frequency Power Amplifier • Complement to KSB1366



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current	3	А
I _B	Base Current	0.3	А
P _C	Collector Power Dissipation (T _C =25°C)	25	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 50 \text{mA}, I_B = 0$	60			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 60V, I_{E} = 0$			100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 7V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.5A$	100		320	
h_{FE2}		$V_{CE} = 5V, I_{C} = 3A$	20			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 2A, I_B = 0.2A$		0.4	1	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = 5V, I_{C} = 0.5A$		0.7	1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 5V, I_{C} = 0.5A$		3		MHz

h_{FE} Classification

Classification	Y	G		
h _{FE1}	100 ~ 200	150 ~ 320		

Typical Characteristics

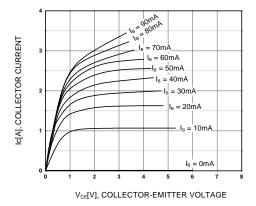


Figure 1. Static Characteristic

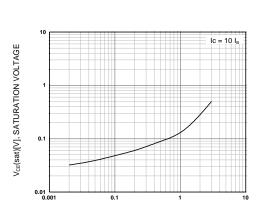


Figure 3. Collector-Emitter Saturation Voltage

I_c[A], COLLECTOR CURRENT

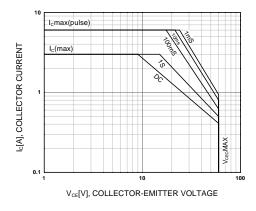


Figure 5. Safe Operating Area

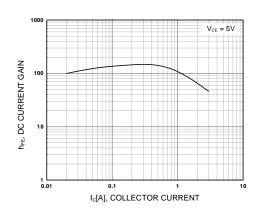


Figure 2. DC current Gain

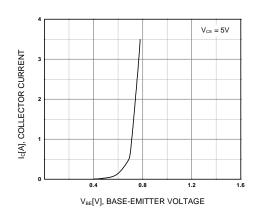


Figure 4. Base-Emitter On Voltage

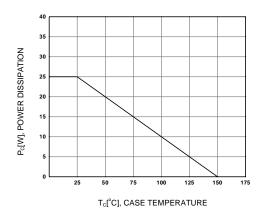
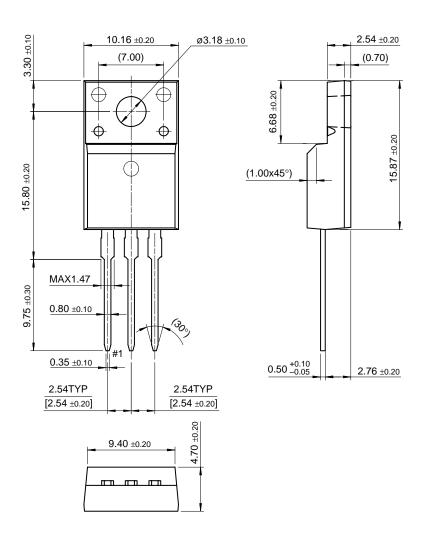


Figure 6. Power Derating

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Package Demensions

TO-220F



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Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information Formative or In Design		This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.		
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.		
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.		

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KSD2012GTU	Full Production	Full Production	\$0.253	TO-220F	3	RAIL	Line 1: \$Y (Fairchild logo) Line 2: D2012-G Line 3: &3	
KSD2012YTU	Full Production	Full Production	\$0.255	TO-220F	3	RAIL	<u>Line 1:</u> \$Y (Fairchild logo) <u>Line 2:</u> D2012-Y <u>Line 3:</u> &3	

KSD2012YYDTU	Full Production	Full Production	\$0.275	<u>TO-220F</u>	3		<u>Line 1:</u> \$Y (Fairchild logo) <u>Line 2:</u> D2012-Y <u>Line 3:</u> &3
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^{*} Fairchild 1,000 piece Budgetary Pricing

** A sample button will appear if the part is available through Fairchild's on-line samples program. If there is no sample button, please contact a Fairchild distributor to obtain samples



Indicates product with Pb-free second-level interconnect. For more information click here.

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